

High purity silicon carbide powders for semiconductor and electronic applications.

High purity silicon carbide produced by the Acheson process for semiconductor and electronic applications. Particularly suitable for PVT crystal growth for SiC wafer manufacturing.

Typical Chemistry

Char. description	Unit	Value
Free C	%	0,02
Free Si	%	0,05
Total O ₂	%	0,04
Size Instrument	Malvern Mastersizer	
Size d10%	µm	204
Size d50%	µm	124
Size d90%	µm	72
Al	ppm	143
Fe	ppm	145
Ni	ppm	30
V	ppm	29
Ca	ppm	10
Ti	ppm	44
N	ppm	14

Analytical Procedures: All measurement is in accordance to FEPA, ANSI or JIS, or other methods in agreement with customers.

Packaging: 25 kg paper bags